

### Description

The HSBB15N15S is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

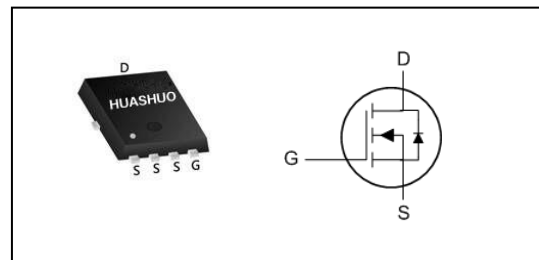
The HSBB15N15S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Super Low Gate Charge
- Green Device Available
- Excellent  $C_{dv/dt}$  effect decline
- Advanced high cell density Trench technology

### Product Summary

$V_{DS}$	150	V
$R_{DS(ON),typ}$	35	m $\Omega$
$I_D$	15	A

### PRPAK3\*3 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	150	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	15	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	9	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	60	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	53	mJ
$I_{AS}$	Avalanche Current	18	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation <sup>3</sup>	45	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	55	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	2.8	$^\circ\text{C/W}$



### Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	150	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	---	35	56	mΩ
	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	41	68	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	---	2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =120V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =120V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =10A	---	33	---	S
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =75V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	19	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	4.5	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.6	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =75V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =10A	---	13	---	ns
T <sub>r</sub>	Rise Time		---	8.2	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	25	---	
T <sub>f</sub>	Fall Time		---	11	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =75V, V <sub>GS</sub> =0V, f=1MHz	---	1090	---	pF
C <sub>oss</sub>	Output Capacitance		---	93	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	6	---	

### Diode Characteristics

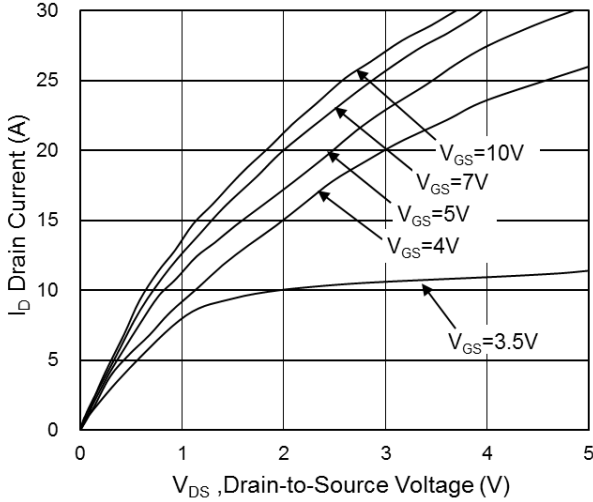
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	15	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	60	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =10A, dI/dt=100A/μs,	---	37	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	263	---	nC

Note :

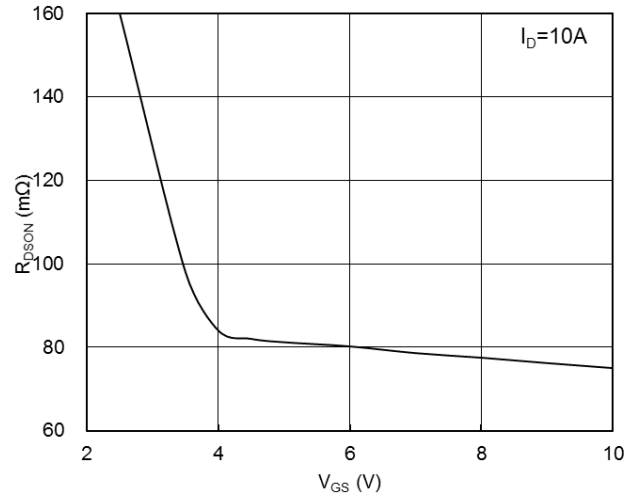
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.3mH,I<sub>AS</sub>=18A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



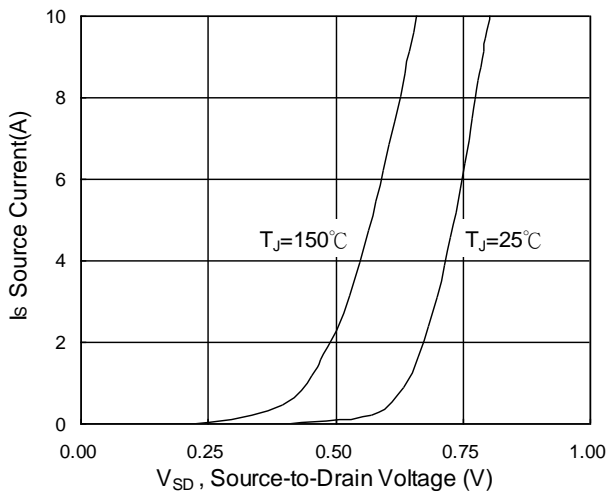
### Typical Characteristics



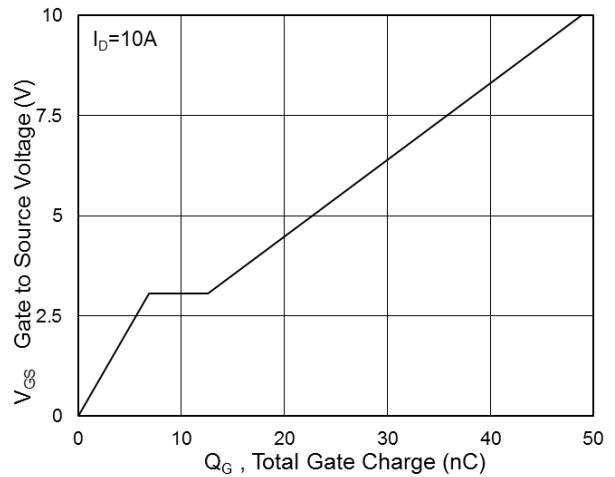
**Fig.1 Typical Output Characteristics**



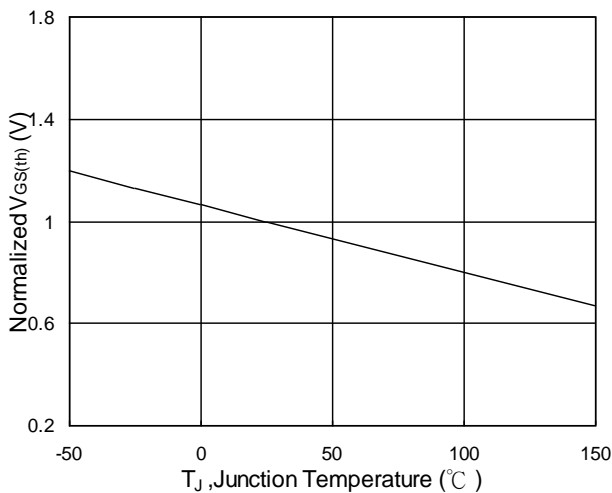
**Fig.2 On-Resistance vs. Gate-Source Voltage**



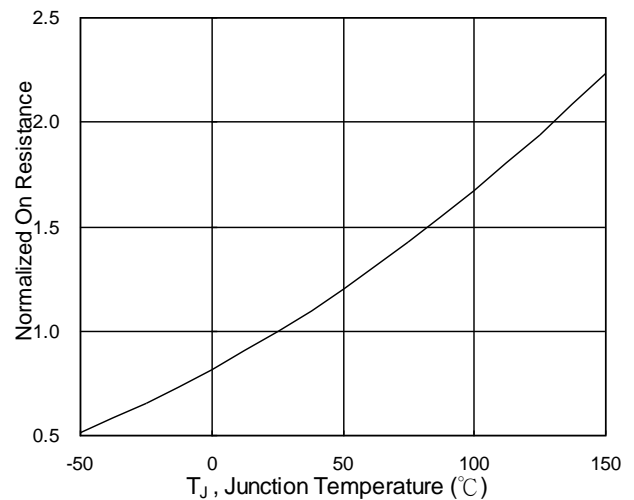
**Fig.3 Forward Characteristics of Reverse**



**Fig.4 Gate-Charge Characteristics**



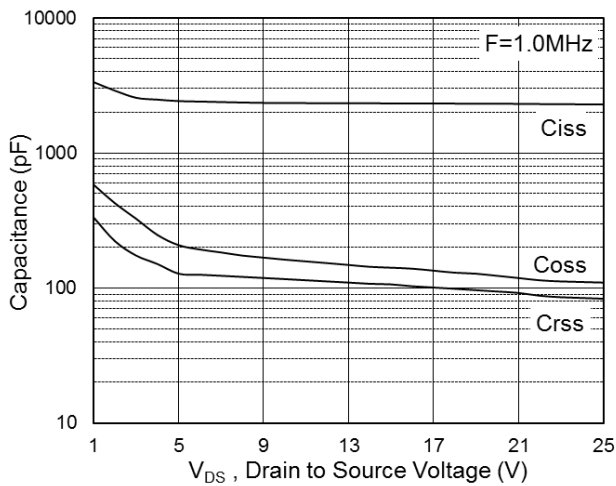
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



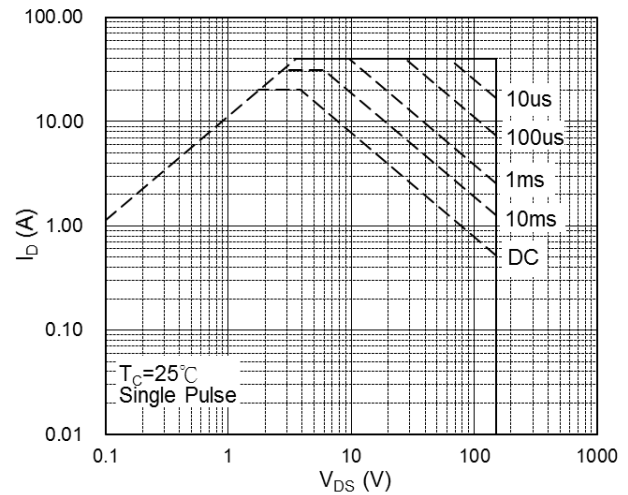
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



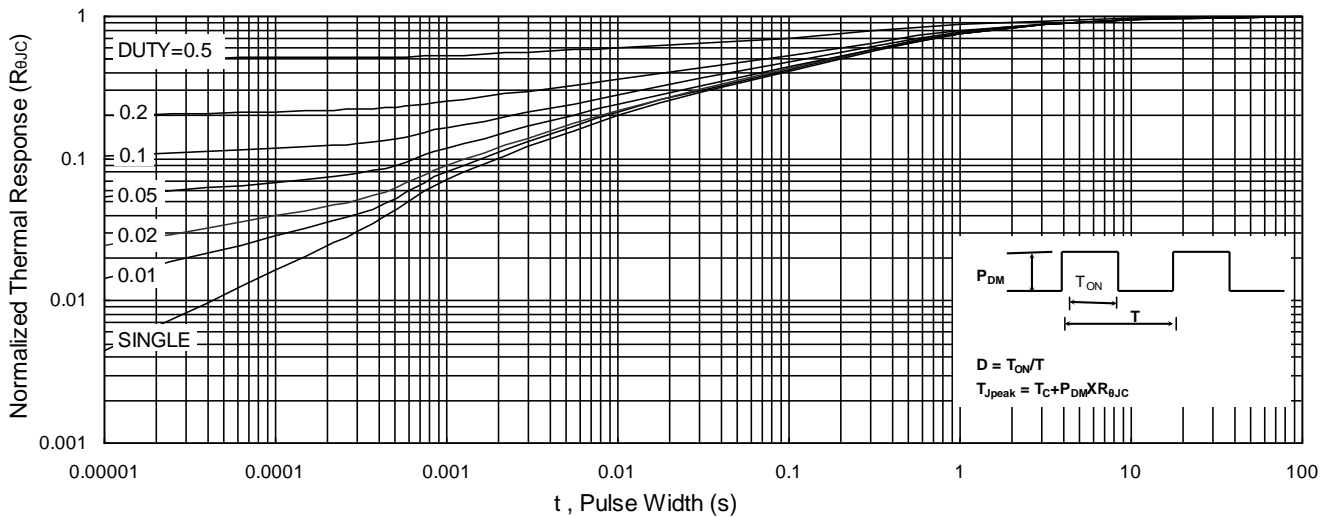
## N-Ch 150V Fast Switching MOSFETs



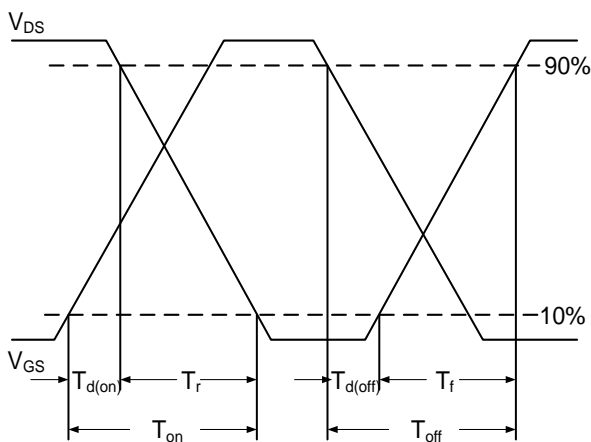
**Fig.7 Capacitance**



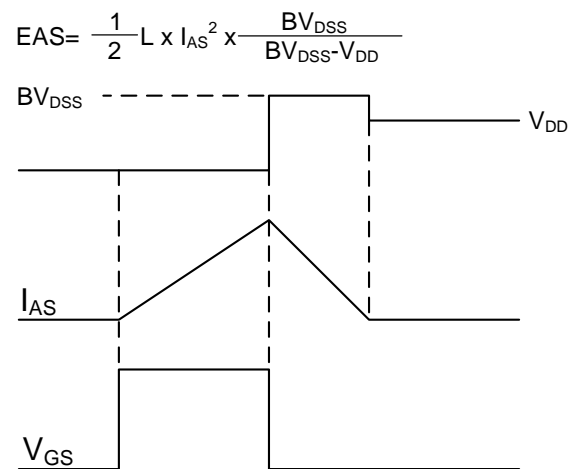
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



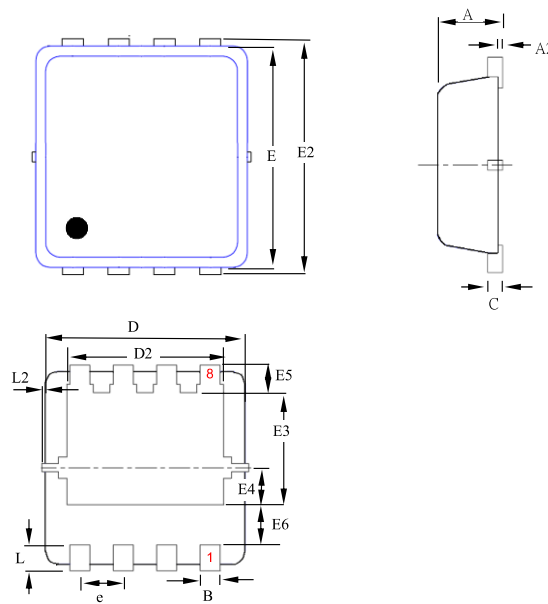
**Fig.11 Unclamped Inductive Switching**



### Ordering Information

Part Number	Package code	Packaging
HSBB15N15S	PRPAK3*3	3000/Tape&Reel

**PRPAK 3\*3(E) Single Outline**



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A2	0.00	—	0.05	0.000	—	0.002
B	0.24	0.30	0.35	0.009	0.012	0.014
C	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.20	0.114	0.118	0.126
D2	2.15	2.35	2.59	0.085	0.093	0.102
E	2.90	3.00	3.12	0.114	0.118	0.123
E2	3.05	3.20	3.45	0.120	0.126	0.136
E3	1.55	1.75	1.95	0.061	0.069	0.077
E4	0.48	0.58	0.68	0.019	0.023	0.027
E5	0.28	0.43	0.58	0.011	0.017	0.023
E6	0.43	0.63	0.87	0.017	0.025	0.034
L	0.30	0.40	0.50	0.012	0.016	0.020
L2	0.00	—	0.10	0.000	—	0.004
e	—	0.65	—	—	0.026	—